HG50N65F1A

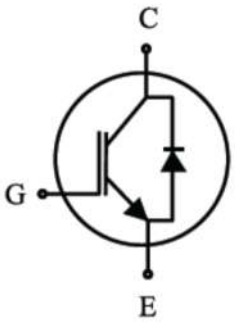
650V /50A Trench Field Stop IGBT

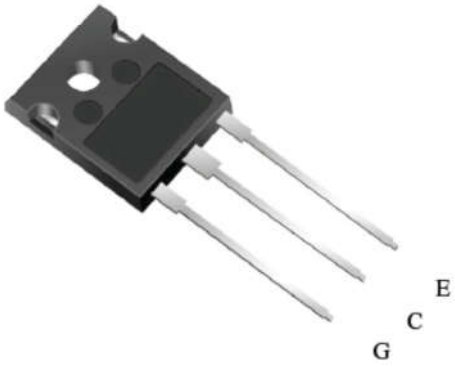
Lu-Semi 650V Trench Field Stop IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for motion control, solar application and welding machine.

V_{CE}	**650**	**V**
I_C	**50**	**A**
$V_{CE(SAT)}$ I_C=50A	**1.8**	**V**

FEATURES

- High breakdown voltage to 650V for improved reliability
- Trench-Stop Technology offering :
  - High speed switching
  - High ruggedness, temperature stable
  - Short circuit withstand time – 5μs
  - Low V_{CEsat}
  - Easy parallel switching capability due to positive temperature coefficient in V_{CEsat}
- Enhanced avalanche capability





APPLICATION

- Uninterruptible Power Supplies
- Inverter
- Welding Converters
- PFC applications
- Converter with high switching frequency

Product	Package	Packaging
HG50N65F1A	TO247	Tube

Maximum Ratings （T_j= 25℃ unless otherwise specified）

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	650	V
DC collector current, limited by $T_j$max T_C = 25°C T_C = 100°C	I_C	 100 50	A
Diode Forward current, limited by $T_j$max T_C = 25°C T_C = 100°C	I_F	 100 50	A
Turn off safe operating area V_{CE} ≤650V, T_j ≤ 150°C		200	A
Short Circuit Withstand Time, V_{GE}= 15V, V_{CE}≤ 400V	T_{sc}	5	μs
Operating junction temperature T_j		-40...+150	°C
Storage temperature	T_s	-55...+150	°C
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT thermal resistance, junction - case	R_{θ}(j-c)	0.48	K/W
Diode thermal resistance, junction - case	R_{θ}(j-c)	1.1	K/W
Thermal resistance, junction - ambient	R_{θ}(j-a)	40	K/W

Electrical Characteristics （T_j= 25℃ unless otherwise specified）

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	V_{GE}=0V , I_C=250uA	650		-	V
		V_{GE}=0V , I_C=1mA	650			V
Gate Threshold Voltage	$V_{GE(th)}$	V_{GE}=V_{CE}, I_C=250uA	4.1	5.0	5.7	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_{GE}=15V, I_C=50A T_j = 25°C T_j = 150°C	- -	1.8 2.0	2.3	V V
Zero gate voltage collector current	I_{CES}	V_{CE} = 650V, V_{GE} = 0V T_j = 25°C T_j = 150°C		0.1	40 1000	μA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = 20V			100	nA

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Dynamic						
Input capacitance	C_{ies}	V_{CE} = 30V, V_{GE} = 0V, f = 1MHz		3300		pF
Output capacitance	C_{oes}			146		
Reverse transfer capacitance	C_{res}			122		

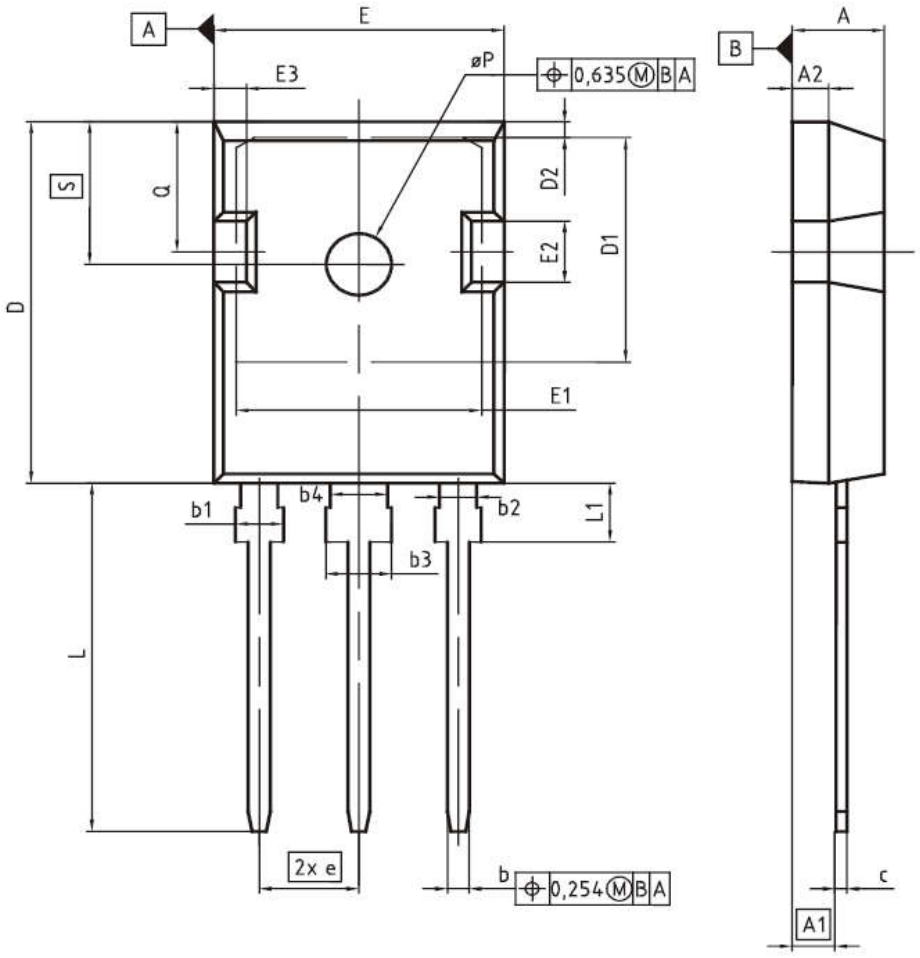
Switching Characteristic, Inductive Load（T_j= 25℃ unless otherwise specified）

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic T_j=25°C						
Turn-on Delay Time	$t_{d(on)}$	T_j=25°C V_{CC} = 400V, I_C = 50.0A, V_{GE} = 0.0/15.0V, Rg=12Ω	-	40	-	ns
Rise Time	t_r		-	22	-	ns
Turn-off Delay Time	$t_{d(off)}$		-	180	-	ns
Fall Time	t_f		-	145	-	ns
Turn-on Energy	E_{on}		-	1.9	-	mJ
Turn-off Energy	E_{off}		-	1.1	-	mJ

Electrical Characteristics of the DIODE（T_j= 25℃ unless otherwise specified）

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						
Diode Forward Voltage	V_{FM}	I_F = 50A	-	2.4	-	V
Reverse Recovery Time	T_{rr}	I_F= 40A, V_R = 300V, di/dt= 600A/μs,	-	90	-	ns
Reverse Recovery Current	I_{rr}		-	17	-	A
Reverse Recovery Charge	Q_{rr}		-	900	-	nC

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248